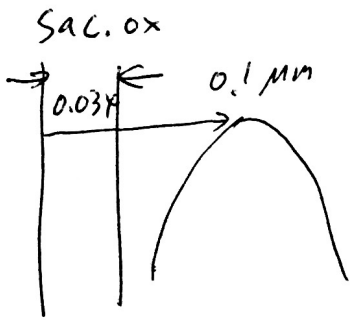


# EE143 HW#11 Solutions

1 a)  $V_{th}$  for NMOS

$V_{th}$  implants @ step 16:  $\Phi_{11}, 30keV, D_I = 9 \times 10^{11} / cm^2$

(Fig 5.3)  $R_p = 0.1 \mu m, \Delta R_p = 0.035 \mu m$



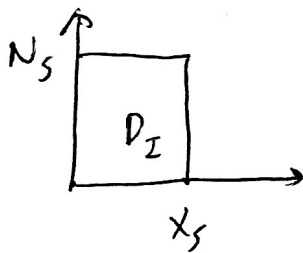
- implantation was an equivalent "DT" as

$$Dt = \frac{1}{2} \Delta R_p^2 = 6.13 \times 10^{-12} cm^2$$

- high temp stops after step 16 (see HW#9)

$$\Sigma Dt = 1.1 \times 10^{-10} cm^2$$

$$\Rightarrow \text{total } Dt = 1.16 \times 10^{-10} cm^2$$



$$N_s = \frac{N_0}{2} = \frac{1}{2} \frac{D_I/2}{\sqrt{\pi Dt}} = 1.18 \times 10^{16} / cm^2$$

$$\therefore x_s = \frac{D_I}{N_s} = 0.76 \mu m$$

approx. as 0.3

need test  $W_{dep}$  w/  $N_s$ :

$$x_{j,N_s} = \sqrt{\frac{2 \epsilon_{si}}{q} \frac{1}{N_s} 2 |\phi_{f,N_s}|}$$

$$V_{th} = V_{FB} - 2 \phi_{f,N_s} - \frac{Q_B}{C_{ox}}$$

$$V_{FB} = \phi_{f,N_s} - \phi_{f,n+gate}$$

$$= 0.3 - 0.56$$

$$= -0.86$$

From page 209  
Jaeger

$$Q_B = - \sqrt{2 \epsilon_{si} \cdot q N_s \cdot 2 |\phi_{f,N_s}|}$$

$$= -4.84 \times 10^{-8} C/cm^2$$

$$C_{ox} = \frac{\epsilon_{102} \epsilon_0}{t_{ox}} = \frac{3.9 \times 8.854 \times 10^{-14}}{59.53 \times 10^{-7} cm} = 5.8 \times 10^{-8} C/V \cdot cm^2$$

$$= \sqrt{\frac{2 \times 11.7 \times 8.854 \times 10^{-14}}{1.6 \times 10^{-19}} \cdot \frac{1}{1.18 \times 10^{16}} \cdot 2 \cdot 0.3}$$

$$= 0.26 \mu m < x_s$$

OK, the  $I_D$  ( $V_{th}$ )

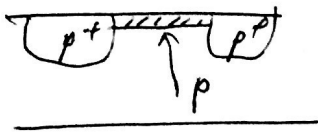
covers all depletion region

assumption is correct

$$V_{th} = -0.86 - (-0.6)$$

$$-(-0.834) = \boxed{0.574 V}$$

## b) PMOS $V_{tp}$



same  $V_{th}$  implants as NMOS (Boron)  
 so S/D are shorted (i.e., current flows)  
 when no bias is applied on gate  
 To operate, need to apply a "+" bias on gate  
 to create depletion region and thus to turn  
 device "off"  $\Rightarrow$  depletion-mode PMOS

$$V_{tp} = V_{FB} - 2\phi_f - \frac{Q_B}{C_{ox}}$$

← the total implants (Boron) since you wanna deplete all the p-type implants

$$V_{tp} = \underbrace{(\phi_s, N_s)}_{\text{approx. } 0.3} - \underbrace{\phi_{fn+gate}}_{\text{same as NMOS case}} - 2\phi_f - \frac{D_E \cdot q}{C_{ox}}$$

$N_s$  is same as that of NMOS

$$= (-0.3 - 0.56) + 0.6 + \frac{9 \times 10^{11} \times 1.6 \times 10^{-19}}{5.8 \times 10^{-8}}$$

$$= \boxed{2.22 \text{ V}}$$

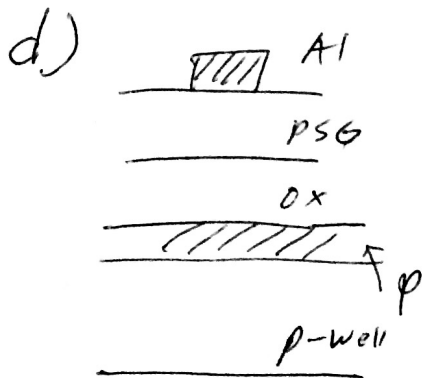
## c) mobility vs. concentration chart

@  $1.18 \times 10^{16} / \text{cm}^3$  ( $N_s$ )

$$\mu_p = 425 \frac{\text{cm}^2}{\text{V}\cdot\text{s}} \quad \mu_n = 1250 \frac{\text{cm}^2}{\text{V}\cdot\text{s}}$$

$$\therefore k_p = \mu_p C_{ox} = 2.47 \times 10^{-5} \text{ F/V}\cdot\text{s}$$

$$k_n = \mu_n C_{ox} = 7.25 \times 10^{-5} \text{ F/V}\cdot\text{s}$$



channel stop implants @ step 10

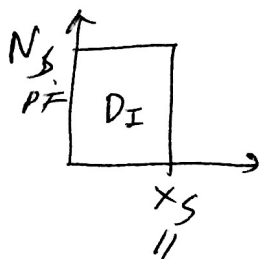
B11, 100keV,  $D_I = 10^{13} / \text{cm}^2$  P-Field Channel stop

$\Rightarrow R_p = 0.32 \mu\text{m}$   $\Delta R_p = 0.07 \mu\text{m}$

$Dt = 2.45 \times 10^{-11} \text{cm}^2$

$\Sigma Dt \text{ afterwards} = 2.43 \times 10^{-10} \text{cm}^2$

$\Rightarrow \text{total } Dt = 2.68 \times 10^{-10} \text{cm}^2$



$N_{s,PF} = \frac{1}{2} N_0 = \frac{1}{2} \frac{D_I / \sqrt{Dt}}{\sqrt{Dt}} = 8.62 \times 10^{16} / \text{cm}^3$

$X_j, N_{s,PF} = \sqrt{\frac{2 \epsilon_{si}}{q} \frac{1}{N_{s,PF}} 2(\phi_f)} = 0.1 \mu\text{m} < X_s$  OK

$\frac{D_I}{N_s} = 1.16 \mu\text{m}$

$V_{th,PF} = V_{FB} - 2\phi_f - \frac{Q_B}{C_{ox}}$   
 $= -0.97 - (-0.6) - \dots$

$1.3 \times 10^{-9} \text{C/cm}^2$

$V_{FB} = \phi_s, N_{s,PF} - \phi_{Al}$

$= -0.3 - (-0.56 - 0.11)$   
 $= -0.97 \text{V}$  page 203

$$\frac{\sqrt{2 \cdot 11.7 \cdot 8.854 \times 10^{-14} \cdot 1.6 \times 10^{-19} \cdot 8.62 \times 10^{16} \cdot 2 \cdot 0.3}}{3.9 (8.854 \times 10^{-14})} \left. \begin{matrix} \phantom{\sqrt{...}} \\ \phantom{\sqrt{...}} \end{matrix} \right\} = 2.46 \times 10^{-9} \text{C/cm}^2$$

assume PSG has the same  $\epsilon$  as  $\text{SiO}_2$

$= 52.86 \text{V}$

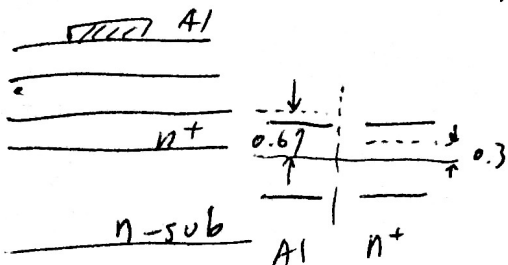
e)  $V_{th, N}$ -field implants @ step 12

P,  $D_I = 5 \times 10^{12} / \text{cm}^2$ , 40keV

$\Rightarrow R_p = 0.05 \mu\text{m}$ ,  $\Delta R_p = 0.022 \mu\text{m} \Rightarrow Dt = 2.42 \times 10^{-12} \text{cm}^2$

$N_s = \frac{1}{2} N_0 = \frac{1}{2} \frac{D_I / \sqrt{Dt}}{\sqrt{Dt}} = 4.52 \times 10^{16} / \text{cm}^3$   $\left( X_j, \text{TEST} < X_s \right)$  verify yourself

$V_{th} = V_{FB} - 2\phi_f - \frac{Q_B}{C_{ox}} = (0.3 - 0.56 - 0.11) - 0.6 - \dots$



$$\frac{\sqrt{2 \cdot 11.7 \cdot 8.854 \times 10^{-14} \cdot 1.6 \times 10^{-19} \cdot 4.52 \times 10^{16} \cdot 2 \cdot 0.3}}{2.46 \times 10^{-9}} = 9.48 \times 10^{-8} \text{C/cm}^2$$

$= -39.51 \text{V}$